

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S76	1	(epitaxial near3 (GaN gallium near nitride)) with (silicon near nitride SiN) with chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:41
S77	181	(epitaxial near3 (GaN gallium near nitride)) with buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:29
S78	501	(epitaxial near3 (GaN gallium near nitride)) with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:35
S79	643	(epitaxial near3 (GaN gallium near nitride)) with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:35
S80	857	S76 or S77 or S78 or S79	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:36
S81	586	S76 or S77 or S78	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:36
S82	147	S81 and chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:37
S83	321	S81 and silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:37
S84	154	S83 and silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:37

S85	154	S84 and (GaN gallium near nitride) with epitaxial\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:39
S86	53	S84 and (silicon near nitride) with epitaxial\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:39
S87	126	S81 and (GaN gallium near nitride) with (silicon near nitride SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:41
S88	1	S87 and (GaN near nitride SiN) with chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:42
S89	0	S87 and (GaN near nitride) with chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:42
S90	19	S87 and (GaN gallium near nitride) with chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:04
S91	4	pyrolytic near silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:10
S92	1128	pyrolytic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:09
S93	7	pyrolytic near5 silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:14
S94	54	pyrolytic near deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:13

S95	0	S94 with passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:12
S96	2	S94 with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:12
S97	4	S94 with silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 09:54
S98	7	"4586243"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:19

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L7	11124	((metal near insulator near semiconductor near field near effect near transistor) MISFET) ((high near electron near mobility near transistor) HEMT)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 17:19
L8	255	(source and drain and gate) near5 ((wet near2 etch\$3) (dry near2 etch\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 17:38
L9	26	7 and 8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 17:21
L10	85	(source and drain and gate) near5 (wet near2 etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:52
L11	2	7 and 10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 17:54
L12	0	11 and dry near2 etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 17:54
L16	0	I10 and (epitaxial near3 (GaN gallium near nitride)) with buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:31
L17	4	I10 and (light near emitting near device LED)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:31
L18	9308	(source and drain and gate) and (wet near2 etch\$3) and (dry near2 etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:54

L19	704	7 and 18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:53
L20	235	passivat\$3 near layer with (source and drain and gate) and (wet near2 etch\$3) and (dry near2 etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:55
L21	4	7 and 20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:55